

Curriculum Vitae

Personal data

First name: **Athanasios**
Surname : **Kostopoulos**
Date of birth: May 26th 1975
Nationality: Greek
Military Service: Fulfilled (2002-2003)
Affiliation: Microelectronics Research Group (MRG)
Institute of Electronic Structure & Laser (IESL)
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Education

1994 - 1999 B.Sc. in Physics, Department of Physics, University of Crete
2000- 2002 M.Sc., Graduate Program of Microelectronics and Optoelectronics, Dept. of Physics, University of Crete

Position

2002 - today Permanent Technical Research staff as a cleanroom process engineer at IESL (Institute of Electronic Structure and Laser), FORTH

Research experience

Participation in the following research projects:

- Advanced MEMS For RF and Millimetre Wave Communications (AMICOM) FP6 – NoE
- DEVELOPMENT AND ANALYSIS OF LEFT-HANDED MATERIALS Project acronym: DALHM. Project number: IST-2001-35511
- Micro and Nano Technologies Based on Wide Band Gap Materials for Future Transmitting Receiving and Sensing Systems (“MERCURE”)-JU ENIAC call 2
- New Generation of GaN-based sensor arrays for nano- and pico-fluidic systems for fast and reliable biomedical testing (GANANO) Project ID: 505641 Funded under: FP6-NMP
- ULTRAGAN Funded under: FP6-NMP
- MoRGaN Funded under: EU FP7
- ESA-GREECE “AVALANCE SIC PHOTODIODES”
- FP7 – NANORF - Carbon Based Smart Systems For wireless applications
- FP7 – NANOTEC – Nanostructured materials and RF-MEMS RFIC/MMIC technologies for highly adaptive and reliable RF systems
- FP7 - SMARTPOWER - Smart integration of GaN & SiC high power electronics for industrial and RF applications
- ENIAC - NANOCOM – Micro and Nano Technologies Based on Wide Band Gap Materials for Future Transmitting Receiving and Sensing Systems

- ENIAC – MERCURE - Micro- and nanotechnologies based on wide band gap materials for future communication and sensing systems
- HORIZON 2020 – CHIRON - Spin Wave Computing for Ultimately-Scaled Hybrid Low-Power Electronics
- EINSTEIN bilateral Greece-Russia collaboration project - Experimental and theoretical studies of physical properties of low dimensional quantum nanoelectronic systems
- EPAnEK 2014-2020 Competence – Entrepreneurship – Innovation - RADAR - Heterogeneous 3D integration employ disruptive nanotechnologies for the next generation of smart power RF T/R modules, Research – Create – Innovate, Co-financed by Greece and the European Union

Teaching Experience

2004 – 2005	Teaching Assistant at Laboratory Lessons
2005 – 2006	Department of Informatics Engineering, Technological Educational
2007 – 2008	Institute of Crete. Courses: Digital Design

Publications

Athanasios Kostopoulos has contributed more 50 research publications in refereed journals. As of May 15, 2019, he has received 639 total citations and his **h-index is 13**, according to Scopus bibliometrics

Extended list of publications

1. Improved GaN Quantum Well Microcavities for Robust Room Temperature Polaritonics

Amargianitakis E.A., Miziou F., Androulidaki M., Tsagaraki K., Kostopoulos A., Konstantinidis G., Delamadeleine E., Monroy, E., Pelekanos N.T.

Physica Status Solidi (B) Basic Research 2019, Article number 1800716

DOI:10.1002/pssb.201800716

2. Long-term stability of transparent n/p ZnO homojunctions grown by rf-sputtering at room-temperature

V. Kampylafka, A. Kostopoulos, M. Modreanu, M. Schmidt, E. Gagaoudakis, K. Tsagaraki, V. Kontomitrou, G. Konstantinidis, G. Deligeorgis, G. Kiriakidis, E. Aperathitis

Journal of Materiomics, Open Access 2019

DOI: <https://doi.org/10.1016/j.jmat.2019.02.006>

3. Multimodal microscopy test standard for scanning microwave, electron, force and optical microscopy

Haessler O.C., Wiegand M.F., Kostopoulos A., Doundoulakis G., Aperathitis E., Fatikow S., Kiriakidis G.

Journal of Micro-Bio Robotics Volume 14, Issue 3-4, 1 December 2018, Pages 51-57

DOI: 10.1007/s12213-018-0108-z

4. GaN Membrane Supported SAW Pressure Sensors with Embedded Temperature Sensing Capability

Muller, A., Konstantinidis, G., Giangu, I., Adam, G.C., Stefanescu, A., Stavriniadis, A., Stavriniadis, G., Kostopoulos A., Boldeiu, G.^a, Dinescu, A.

IEEE Sensors Journal Volume 17, Issue 22, 15 November 2017, Article number 8052477,
Pages 7383-7393
DOI: 10.1109/JSEN.2017.2757770

5. Test standard for light, electron & microwave microscopy to enable robotic processes (Conference Paper)

Haenssler, O.C., Kostopoulos, A., Doundoulakis, G., Aperathitis, E., Fatikow, S., Kiriakidis, G.

International Conference on Manipulation, Automation and Robotics at Small Scales, MARSS 2017 – Proceedings 3 August 2017, Article number 80019071st International Conference on Manipulation, Automation and Robotics at Small Scales, MARSS 2017; Montreal; Canada; 17 July 2017 through 21 July 2017; Category number CFP17D58-ART; Code 129786

DOI: 10.1109/MARSS.2017.8001907

6. Investigation of thin InN/GaN heterostructures with in situ SiN_x dielectric grown by plasma-assisted molecular beam epitaxy

Zervos C, Adikimenakis A, Beleniotis P, Kostopoulos, A., Androulidaki M, Tsagaraki K, Kayambaki M, Konstantinidis G, Georgakilas, A.

Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics Volume 35, Issue 2, 1 March 2017, Article number 021210

DOI: 10.1116/1.4977606

7. “Effect of rapid thermal annealing on polycrystalline InGaN thin films deposited on fused silica substrate”

S.A. Kazazis, E. Papadomanolaki, M. Androulidaki, K. Tsagaraki, A. Kostopoulos, E. Aperathitis, E. Iliopoulos

Thin Solid Films 611 (2016) 46–51,

DOI: 10.1016/j.tsf.2016.04.045

8. “In-situ SiN_x/InN structures for InN channel transistors”,

Ch. Zervos, A. Adikimenakis, P. Beleniotis, A. Kostopoulos, K. Tsagaraki, M. Kayambaki, G. Konstantinidis, and A. Georgakilas,

Appl. Phys. Lett. Volume 108, Issue 14, 142102, 5 April 2016

DOI: 10.1063/1.4945668

9. “Analysis of current instabilities of thin AlN/GaN/AlN double heterostructure high electron mobility transistors”,

Ch. Zervos, A. Adikimenakis, A. Bairamis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis, and A. Georgakilas,

Semiconductor Science and Technology, 31, 065002, 5 April 2016

DOI: 10.1088/0268-1242/31/6/065002

10. Electron density and currents of AlN/GaN high electron mobility transistors with thin GaN/AlN buffer layer.

Bairamis A., Zervos C., Adikimenakis A., Kostopoulos, A., Kayambaki, M., Tsagaraki, K., Konstantinidis, G., Georgakilas, A.

Applied Physics Letters, Volume 105, Issue 11, 15 September 2014, Article number 113508

DOI: 10.1063/1.4896026

11. AlN/GaN/AlN double heterostructures with thin AlN top barriers

Zervos, Ch., Bairamis, A., Adikimenakis, A., Kostopoulos, A., Kayambaki, M., Tsagaraki, K., Konstantinidis G, Georgakilas, A.

10th International Conference on Advanced Semiconductor Devices and Microsystems, 24 December 2014, Article number 6998659, Pages 113-116, ASDAM

DOI: 10.1109/ASDAM.2014.6998659

12. Graphene-like metal-on-silicon field-effect transistor

Dragoman, M., Konstantinidis, G., Tsagaraki, K., Kostopoulos, T., Dragoman, D., Neculoiu, D.Neculoiu

Nanotechnology 23 (30) , art. no. 305201 (2012)

DOI: 10.1088/0957-4484/23/30/305201

13. ZnO-based diodes fabricated from a single sputtering target

V. Kampylafka, K. Tsagaraki, M. Androulidaki, A. Kostopoulos, M. Kayambaki, M. Modreanu, G. Kiriakidis, E. Aperathitis,

Presented at the European Materials Research Society, E-MRS 2012 Spring Meeting, Symposium: Q Novel materials and fabrication methods for new emerging devices, Strasbourg, May 14-18, 2012.

DOI: 10.1109/SMICND.2011.6095792

14. Zinc Nitride based Optoelectronic Devices

V. Kambilafka, M. Kayambaki, A. Kostopoulos, M. Androulidaki, K. Tsagaraki, M. Modreanu, G. Kiriakidis and E. Aperathitis,

4th International Symposium on Transparent Conductive Materials (TCM 2012), 21 – 25 October, 2012, Creta Maris Hotel, Hersonissos, Crete, Greece.

15. “The effect of power on rf sputtered nitrogen- doped ZnO thin films”,

V. Kambilafka, M. Androulidaki, A. Kostopoulos, K. Tsagaraki, G. Kiriakidis, and E. Aperathitis,

4th International Symposium on Transparent Conductive Materials (TCM 2012), 21 – 25 October, 2012, Creta Maris Hotel, Hersonissos, Crete, Greece.

16. ZnO thin films formed from ZnN target by RF sputtering: From materials to devices

Kampylafka, V., Kostopoulos, A., Androulidaki, M., Tsagaraki K., Modreanu, M., Aperathitis, E.

Proceedings of the International Semiconductor Conference, CAS Volume 2, 2011, Article number 6095792, Pages 279-282, 34th International Semiconductor Conference, CAS 2011, Sinaia 17 October 2011 - 19 October 2011

DOI:10.1109/smicnd.2011.6095792

17. Transparent p/n diode device from a single zinc nitride sputtering target

Kambilafka, V., Kostopoulos, A., Androulidaki, M., Tsagaraki, K., Modreanu, M., Aperathitis, E

Thin Solid Films Volume 520, Issue 4, 1 December 2011, Pages 1202-1206

DOI: 10.1016/j.tsf.2011.06.072

18. Bragg polariton luminescence from a GaN membrane embedded in all dielectric microcavity

Trichas, E., Pelekanos, N.T., Iliopoulos, E., Monroy, E., Tsagaraki, K., Kostopoulos, A., Savvidis, P.G.

19. MEMS switch for 60 GHz band

Vasilache, D., Constantinidis, G., Dragoman, M., Takacs, A., Vladoianu, F., Kostopoulos, T., Boldeiu, G., Moagar, V., Tibeica, C., Bary, L., Plana, R.

Proceedings of SPIE - The International Society for Optical Engineering Volume 7821, 2010, Article number 782100 Advanced Topics in Optoelectronics, Microelectronics, and Nanotechnologies V; Constanta 26-19 August 2010, Code83561

20. High electron mobility transistors based on the AlN/GaN heterojunction

Adikimenakis, A., Aretouli, K.E., Iliopoulos, E., Kostopoulos, A., Tsagaraki, K., Konstantinidis, G., Georgakilas, A.

Microelectronic Engineering 86 (2009) 1071-1073

DOI: 10.1016/j.mee.2009.02.004

21. GaN membrane-supported UV photodetector manufactured using nanolithographic processes

A. Mueller, G. Konstantinidis, G., M. Dragoman, D. Neculoiu, A. Dinescu, M. Androulidaki, M. Kayambaki, A. Stavriniadis, D. Vasilache, C. Buiculescu, I. Petrini, A. Kostopoulos, D. Dascalu

Microelectronic Journal 40 (2009) pp. 319-321

DOI: 10.1016/j.mejo.2008.07.021

22. Rf nems based on carbon nanotubes and graphene (Conference Paper)

Dragoman, M., Konstantinidis, G., Dragoman, D., Neculoiu, D., Cismaru, A., Coccetti, F., Plana, R., Harnagel, H., Kostopoulos, A., Buiculescu, R.

Proceedings of the International Semiconductor Conference, CAS Volume 1, 2008, Article number 4703339, Pages 103-106 2008 International Semiconductor Conference, CAS 2008; Sinaia; Romania; 13 October 2008 through 15 October 2008; Category number CFP08CAS-PRT; Code 77492

DOI: 10.1109/SMICND.2008.4703339

23. Ultraviolet MSM photodetector based on GaN micromachining

Müller, A., Konstantinidis, G., Dragoman, M., Neculoiu, D., Dinescu, A., Androulidaki, M., Kayambaki, M., Stavriniadis, A., Vasilache, D., Buiculescu, C., Petrini, I., Anton, C., Dascalu, D., Kostopoulos, A.

Proceedings of the International Semiconductor Conference, CAS

Volume 1, 2008, Article number 4703336, Pages 91-94 2008 International Semiconductor Conference, CAS 2008; Sinaia; Romania; 13 October 2008 through 15 October 2008; Category number CFP08CAS-PRT; Code 77492

DOI: 10.1109/SMICND.2008.4703336

24. Negative index short-slab pair and continuous wires metamaterials in the far infrared regime

Gundogdu, T. F., Katsarakis, N., Kafesaki, M., Penciu, R. S., Konstantinidis, G., Kostopoulos, A., Economou, E. N., Soukoulis, C. M.

Optics Express Vol. 16, issue: 12 pp. 9173-9180, June 9 2008

DOI: 10.1364/OE.16.009173

25. Multiple negative resistances in trenched structures bridged with carbon nanotubes

Dragoman, M., Konstantinidis, G., Kostopoulos, A., Dragoman, D., Neculoiu, D., Buiculescu, R., Plana, R., Coccetti, F., Hartnagel, H
Applied Physics Letters Volume: 93, Issue: 4, Article Number: 043117, JUL 28 2008
DOI: 10.1063/1.2963367

26. Metallic bonding methodology for heterogeneous integration of optoelectronic dies to CMOS circuits

Robogiannakis P., Kyriakis-Bitzaros, E. D., Minogiou K., Katsafouros S., Kostopoulos A., Konstantinidis G., Halkias, G.
Microelectronic Engineering, Vol:85, Is:4, pp: 727-732, APR 2008
DOI: 10.1016/j.mee.2008.01.053

27. GaN membrane metal-semiconductor-metal ultraviolet photodetector

Muller, A., Konstantinidis, G., Dragoman, M., Neculoiu, D., Kostopoulos, A., Androulidaki, M., Kayambaki, M., Vasilache, D.
Applied Optics, Volume: 47, Issue: 10, Pages: 1453-1456, APR 1 2008
DOI: 10.1364/AO.47.001453

28. Gate-lag and drain-lag effects in (GaN)/InAlN/GaN and InAlN/AlN/GaN HEMTs

J. Kuzmik, J.-F. Carlin, M. Gonschorek, A. Kostopoulos, G.Konstantinidis, G. Pozzovivo, S. Golka, A. Georgakilas, N. Grandjean, G. Strasser and D. Pogany
phys. stat. sol. (a) 204, No. 6, 2019–2022 (2007)
DOI: 10.1002/pssa.200674707

29. Microwave FBAR structures fabricated using micromachined GaN membranes

Neculoiu, D., Konstantinidis, G., Müller, A., Kostopoulos, A., Vasilache, D., Mutamba, K., Sydlo, C., Hartnagel, H.L., Bary, L., Plana, R.
IEEE MTT-S International Microwave Symposium, IMS 2007; Honolulu, HI; United States; 3 June 2007 through 8 June 2007; Category number 07CH37842C; Code 70323, Article number 4263961, Pages 877-880
DOI: 10.1109/MWSYM.2007.380119

30. Membrane supported AlN FBAR structures obtained by micromachining of high resistivity silicon

Neculoiu, D., Vasilache, D., Konstantinidis, G., Morosanu, C., Stavrinidis, A., Kostopoulos, A., Cismaru, A., Buiculescu, C., Petrini, I., Müller, A.
2007 International Semiconductor Conference, CAS 2007; Sinaia; Romania; 15 October 2007 through 17 October 2007; Category number 07TH8934; Code 72877, Volume 1, 2007, Article number 4519705, Pages 293-296
DOI: 10.1109/SMICND.2007.4519705

31. GaN membrane MSM ultraviolet photodetectors

Muller, A., Konstantinidis, G., Kostopoulos, A., Dragoman, M., Neculoiu, D., Androulidaki, M., Kayambaki, M., Vasilache, D., Buiculescu, C., Petrini, I.
Proceedings of SPIE - The International Society for Optical Engineering, Volume 6415, 2007, Article number 641509, Micro- and Nanotechnology: Materials, Processes, Packaging, and Systems III; Adelaide; Australia; 11 December 2006 through 13 December 2006; Code 69479
DOI: 10.1117/12.695086

32. Growth Optimization of an Electron Confining InN/GaN Quantum Well Heterostructure

E. Dimakis, E. Iliopoulos, M. Kayambaki, K. Tsagaraki, A. Kostopoulos, G. Konstantinidis and A. Georgakilas

33. Heterogeneous integration technique of optoelectronic dies to CMOS circuits via metallic bonding (Conference Paper)

Robogiannakis, P., Kyriakis-Bitzaros, E.D., Minoglou, K., Katsafouros, S., Kostopoulos, A., Konstantinidis, G., Halkias, G.

ESTC 2006 - 1st Electronics Systemintegration Technology Conference Volume 1, 2007, Article number 4060744, Pages 328-333 ESTC 2006 - 1st Electronics Systemintegration Technology Conference; Dresden, Saxony; Germany; 5 September 2006 through 7 September 2006; Category number 06EX1494; Code 71926

DOI: 10.1109/ESTC.2006.280020

34. 60 GHz band RF mems switch

Vasilache, D., Dragoman, M., Constantinidis, G., Psychias, Y., Vladoianu, F., Kostopoulos, T., Tibeica, C., Bary, L., Cismaru, A., Neculoiu, D., Buiculescu, C., Petrini, I., Plana, R., Müller, A.

2006 International Semiconductor Conference (Vol.1) Sinaia 27-29 Sept. 2006 Page(s):119 – 122, ISSN:1545-827X, IEEE

35. “GaN micromachined FBAR structures for microwave applications”

Müller A., D. Neculoiu, D. Vasilache, D. Dascalu, G. Konstantinidis, A. Kostopoulos, A. Adikimenakis, A. Georgakilas, K. Mutamba, C. Sydlo, H. L. Hartnagel, A. Dadgar

“Superlattices and Microstructures” (Elsevier) 40, 2006, pp426-431

DOI: 10.1016/j.spmi.2006.07.014

36. InAlN/(In)GaN HEMTs for high power application

J.Kuzmic, J-F. Carlin, A. Kostopoulos, G. Konstantinidis, S.Bychikhin, A.Georgakilas, D. Pogany

MIKON 2006, Workshop on GaN Devices, May 25 2006, Krakow, Poland, pp. 110-124 (Invited)

37. “Experimental demonstration of negative magnetic permeability in the far-infrared frequency regime”

T.F. Gundoglu, I. Tsiapa, A. Kostopoulos, G. Konstantinidis, N. Katsarakis, E.N. Economou, Th. Koschny and C.M. Soukoulis

Applied Physics Letters Vol. 89, 24 August 2006

DOI: 10.1063/1.2335955

38. “New development of GaN membranes based FBAR structures”

D. Neculoiu, Müller A., D. Vasilache, D. Dascalu, G. Konstantinidis, A. Kostopoulos, A. Adikimenakis, A. Georgakilas, K. Mutamba, C. Sydlo, H. L. Hartnagel.

Proc of the MEMSWAVE Conference, Orvieto, Italy, 2006, pp.51-54.

39. InAlN/GaN HEMTs: A first into technological optimization

J.Kuzmic, A. Kostopoulos, G. Konstantinidis, J-F. Carlin, A.Georgakilas, D. Pogany

Transactions on Electron Devices (TED), **IEEE**, Vol. 53, No. 3, pp. 422-426, March 2006

DOI: 10.1109/TED.2005.864379

40. “Micromachined GaN-based FBAR Structures for Microwave Applications”

K. Mutamba, D. Neculoiu, A. Müller, G. Konstantinidis, D. Vasilache, C. Syblo, A. Kostopoulos, A. Adikimenakis, A. Georgakilas, H. L. Hartnagel

Proc of Asia Pacific Microwave Conference, Yokohama, Dec2006, pp.3-1757-1760.

DOI: 10.1109/APMC.2006.4429749

41. “Response to anions of AlGaN/GaN high- electrons- mobility transistors”

Y. Alifragis, A. Georgakilas, G. Konstantinidis, E. Iliopoulos, A. Kostopoulos, N. A. Chaniotakis

Applied Physics Letters Vol. 87, 15 December 2005

DOI: 10.1063/1.2149992

42. “Magnetic response of split-ring resonators in the far infrared frequency regime”

N. Katsarakis, G. Konstantinidis, A. Kostopoulos, R.S. Penciu, T.F. Gundoglu, Th. Koschny, M. Kafesaki, E.N. Economou, and C.M. Soukoulis

Optics Letters, Volume 30, Issue 11, pp. 1348-1350, June 2005

DOI: 10.1364/OL.30.001348

43. Metallic bonding of optoelectronic dies to silicon wafers

Minoglou, K., Kyriakis-Bitzaros, E.D., Grivas, E., Katsafouros, S., Kostopoulos, A., Konstadinidis, G., Halkias, G.

Journal of Physics: Conference Series, Volume 10, Issue 1, 1 January 2005, Pages 393-396

DOI: 10.1088/1742-6596/10/1/096

44. “Technology, Properties and Limitation of State-of-the-art InAlN/GaN HEMTs”

J.Kuzmic, J-F. Carlin, T. Kostopoulos, G. Konstantinidis, , A.Georgakilas, D. Pogany

63rd Device Research Conference (DRC '05), Conference digest pp.57-58, Santa Barbara, June 20-22, 2005

45. “An investigation into the charge distribution and barrier profile tailoring in AlGaN/GaN double heterostructures by self-consistent Poisson-Schrödinger calculations and capacitance-voltage profiling”

M. Zervos, A. Kostopoulos, G. Constantinidis, M. Kayambaki and A. Georgakilas

J. Appl. Phys. Vol. 91, Num. 7, 4387-4393, 1 April 2002

DOI: 10.1063/1.1459604

46. “Control of the polarity of molecular-beam-epitaxy-grown GaN thin films by the surface nitridation of Al₂O₃ (0001) substrates”

S. Mikroulis, A. Georgakilas, A. Kostopoulos, V. Cimalla and E. Dimakis

Applied Physics Letters Vol. 80, Num.16, 2886-2888, 22 April 2002

DOI: 10.1063/1.1472481

47. “The pinch-off behavior, charge distribution and current transport in AlGaN/GaN double heterojunction HFETs”

M. Zervos, A. Kostopoulos, G. Constantinidis, M. Kayambaki, S. Mikroulis, N. Flytzanis and A. Georgakilas

Phys. Stat. Sol.(a) 188, No. 1, 259-262 (2001)

DOI: 10.1002/1521-396X(200111)188:1<259::AID-PSSA259>3.0.CO;2-5

48. “Effects of the sapphire nitridation on the polarity and properties of Ga layers grown by plasma-assisted MBE”

A. Georgakilas, S. Mikroulis, V. Cimalla, M. Zervos, A. Kostopoulos, M. Androulidaki, Ph. Komninou, Th. Kehagias and Th. Karakostas

Phys. Stat. Sol.(a) 188, No. 2, 567-570 (2001)

DOI: 10.1002/1521-396X(200112)188:2<567::AID-PSSA567>3.0.CO;2-W

49. Investigation of the nitridation of Al₂O₃ (0001) substrates by a nitrogen radio frequency plasma source

S. Mikroulis, V. Cimalla, A. Kostopoulos, G. Constantinidis, G. Drakakis, M. Zervos, M.Cengher and A. Georgakilas,
Procc. of MMN 2000, Athens 20-22, 2000, pp.135- 138

50. Atomic force microscopy analysis of Ga-face and N-face GaN grown on Al₂O₃ (0001) by plasma-assisted molecular beam epitaxy

Kostopoulos, A., Mikroulis, S., Dimakis, E., Tsagaraki, K., Constantinidis, G., Georgakilas, A.
ASDAM 2000 - Conference Proceedings: 3rd International Euro Conference on Advanced Semiconductor Devices and Microsystems2000, Article number 889519, Pages 355-3583rd International Euro Conference on Advanced Semiconductor Devices and Microsystems, ASDAM 2003; Smolenice Castle Smolenice; Slovakia; 16 October 2000 through 18 October 2000; Category number00EX386; Code 116662
DOI: 10.1109/ASDAM.2000.889519

51. Material properties of GaN films with Ga- or N- face polarity grown by MBE on Al₂O₃ (0001) substrates under different growth conditions.

A. Kostopoulos, S. Mikroulis, E. Dimakis, E-M Pavelescu, M Andrulidaki, K Tsagaraki, G. Constantinidis, A. Georgakilas,
Procc. of MMN 2000, Athens 20-22, 2000, pp.201- 204